

4.0 DATA EEPROM AND FLASH PROGRAM MEMORY

The Data EEPROM and FLASH Program Memory are readable and writable during normal operation over the entire VDD range. These operations take place on a single byte for Data EEPROM memory and a single word for Program memory. A write operation causes an erase-then-write operation to take place on the specified byte or word. A bulk erase operation may not be issued from user code (which includes removing code protection).

Access to program memory allows for checksum calculation. The values written to program memory do not need to be valid instructions. Therefore, up to 14-bit numbers can be stored in memory for use as calibration parameters, serial numbers, packed 7-bit ASCII, etc. Executing a program memory location containing data that form an invalid instruction, results in the execution of a NOP instruction.

The EEPROM Data memory is rated for high erase/write cycles (specification D120). The FLASH program memory is rated much lower (specification D130), because EEPROM data memory can be used to store frequently updated values. An on-chip timer controls the write time and it will vary with voltage and temperature, as well as from chip to chip. Please refer to the specifications for exact limits (specifications D122 and D133).

A byte or word write automatically erases the location and writes the new value (erase before write). Writing to EEPROM data memory does not impact the operation of the device. Writing to program memory will cease the execution of instructions until the write is complete. The program memory cannot be accessed during the write. During the write operation, the oscillator continues to run, the peripherals continue to function and interrupt events will be detected and essentially “queued” until the write is complete. When the write completes, the next instruction in the pipeline is executed and the branch to the interrupt vector will take place, if the interrupt is enabled and occurred during the write.

Read and write access to both memories take place indirectly through a set of Special Function Registers (SFR). The six SFRs used are:

- EEDATA
- EEDATH
- EEADR
- EEADRH
- EECON1
- EECON2

The EEPROM data memory allows byte read and write operations without interfering with the normal operation of the microcontroller. When interfacing to EEPROM data memory, the EEADR register holds the address to be accessed. Depending on the operation, the EEDATA register holds the data to be written, or the data read, at the address in EEADR. The PIC16F873/874 devices have 128 bytes of EEPROM data memory and therefore, require that the MSb of EEADR remain clear. The EEPROM data memory on these devices do not wrap around to 0, i.e., 0x80 in the EEADR does not map to 0x00. The PIC16F876/877 devices have 256 bytes of EEPROM data memory and therefore, uses all 8-bits of the EEADR.

The FLASH program memory allows non-intrusive read access, but write operations cause the device to stop executing instructions, until the write completes. When interfacing to the program memory, the EEADRH:EEADR registers form a two-byte word, which holds the 13-bit address of the memory location being accessed. The register combination of EEDATH:EEDATA holds the 14-bit data for writes, or reflects the value of program memory after a read operation. Just as in EEPROM data memory accesses, the value of the EEADRH:EEADR registers must be within the valid range of program memory, depending on the device: 0000h to 1FFFh for the PIC16F873/874, or 0000h to 3FFFh for the PIC16F876/877. Addresses outside of this range do not wrap around to 0000h (i.e., 4000h does not map to 0000h on the PIC16F877).

4.1 EECON1 and EECON2 Registers

The EECON1 register is the control register for configuring and initiating the access. The EECON2 register is not a physically implemented register, but is used exclusively in the memory write sequence to prevent inadvertent writes.

There are many bits used to control the read and write operations to EEPROM data and FLASH program memory. The EEPGD bit determines if the access will be a program or data memory access. When clear, any subsequent operations will work on the EEPROM data memory. When set, all subsequent operations will operate in the program memory.

Read operations only use one additional bit, RD, which initiates the read operation from the desired memory location. Once this bit is set, the value of the desired memory location will be available in the data registers. This bit cannot be cleared by firmware. It is automatically cleared at the end of the read operation. For EEPROM data memory reads, the data will be available in the EEDATA register in the very next instruction cycle after the RD bit is set. For program memory reads, the data will be loaded into the EEDATH:EEDATA registers, following the second instruction after the RD bit is set.

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Write operations have two control bits, WR and WREN, and two status bits, WRERR and EEIF. The WREN bit is used to enable or disable the write operation. When WREN is clear, the write operation will be disabled. Therefore, the WREN bit must be set before executing a write operation. The WR bit is used to initiate the write operation. It also is automatically cleared at the end of the write operation. The interrupt flag EEIF is used to determine when the memory write completes. This flag must be cleared in software before setting the WR bit. For EEPROM data memory, once the WREN bit and the WR bit have been set, the desired memory address in EEADR will be erased, followed by a write of the data in EEDATA. This operation takes place in parallel with the microcontroller continuing to execute normally. When the write is complete, the EEIF flag bit will be set. For program memory, once the WREN bit and the WR bit have been set, the microcontroller will cease to exe-

cute instructions. The desired memory location pointed to by EEADRH:EEADR will be erased. Then, the data value in EEDATH:EEDATA will be programmed. When complete, the EEIF flag bit will be set and the microcontroller will continue to execute code.

The WRERR bit is used to indicate when the PIC16F87X device has been reset during a write operation. WRERR should be cleared after Power-on Reset. Thereafter, it should be checked on any other RESET. The WRERR bit is set when a write operation is interrupted by a MCLR Reset, or a WDT Time-out Reset, during normal operation. In these situations, following a RESET, the user should check the WRERR bit and rewrite the memory location, if set. The contents of the data registers, address registers and EEPGD bit are not affected by either MCLR Reset, or WDT Time-out Reset, during normal operation.

REGISTER 4-1: EECON1 REGISTER (ADDRESS 18Ch)

R/W-x	U-0	U-0	U-0	R/W-x	R/W-0	R/S-0	R/S-0
EEPGD	—	—	—	WRERR	WREN	WR	RD
bit 7							bit 0

- bit 7 **EEPGD:** Program/Data EEPROM Select bit
1 = Accesses program memory
0 = Accesses data memory
(This bit cannot be changed while a read or write operation is in progress)
- bit 6-4 **Unimplemented:** Read as '0'
- bit 3 **WRERR:** EEPROM Error Flag bit
1 = A write operation is prematurely terminated
(any MCLR Reset or any WDT Reset during normal operation)
0 = The write operation completed
- bit 2 **WREN:** EEPROM Write Enable bit
1 = Allows write cycles
0 = Inhibits write to the EEPROM
- bit 1 **WR:** Write Control bit
1 = Initiates a write cycle. (The bit is cleared by hardware once write is complete. The WR bit can only be set (not cleared) in software.)
0 = Write cycle to the EEPROM is complete
- bit 0 **RD:** Read Control bit
1 = Initiates an EEPROM read. (RD is cleared in hardware. The RD bit can only be set (not cleared) in software.)
0 = Does not initiate an EEPROM read

Legend:

R = Readable bit	W = Writable bit	U = Unimplemented bit, read as '0'
- n = Value at POR	'1' = Bit is set	'0' = Bit is cleared x = Bit is unknown

4.2 Reading the EEPROM Data Memory

Reading EEPROM data memory only requires that the desired address to access be written to the EEADR register and clear the EEPGD bit. After the RD bit is set, data will be available in the EEDATA register on the very next instruction cycle. EEDATA will hold this value until another read operation is initiated or until it is written by firmware.

The steps to reading the EEPROM data memory are:

1. Write the address to EEDATA. Make sure that the address is not larger than the memory size of the PIC16F87X device.
2. Clear the EEPGD bit to point to EEPROM data memory.
3. Set the RD bit to start the read operation.
4. Read the data from the EEDATA register.

EXAMPLE 4-1: EEPROM DATA READ

```
BSF    STATUS, RP1    ;
BCF    STATUS, RP0    ;Bank 2
MOVF   ADDR, W        ;Write address
MOVWF  EEADR          ;to read from
BSF    STATUS, RP0    ;Bank 3
BCF    EECON1, EEPGD  ;Point to Data memory
BSF    EECON1, RD     ;Start read operation
BCF    STATUS, RP0    ;Bank 2
MOVF   EEDATA, W      ;W = EEDATA
```

4.3 Writing to the EEPROM Data Memory

There are many steps in writing to the EEPROM data memory. Both address and data values must be written to the SFRs. The EEPGD bit must be cleared, and the WREN bit must be set, to enable writes. The WREN bit should be kept clear at all times, except when writing to the EEPROM data. The WR bit can only be set if the WREN bit was set in a previous operation, i.e., they both cannot be set in the same operation. The WREN bit should then be cleared by firmware after the write. Clearing the WREN bit before the write actually completes will not terminate the write in progress.

Writes to EEPROM data memory must also be prefaced with a special sequence of instructions, that prevent inadvertent write operations. This is a sequence of five instructions that must be executed without interruptions. The firmware should verify that a write is not in progress, before starting another cycle.

The steps to write to EEPROM data memory are:

1. If step 10 is not implemented, check the WR bit to see if a write is in progress.
2. Write the address to EEADR. Make sure that the address is not larger than the memory size of the PIC16F87X device.
3. Write the 8-bit data value to be programmed in the EEDATA register.
4. Clear the EEPGD bit to point to EEPROM data memory.
5. Set the WREN bit to enable program operations.
6. Disable interrupts (if enabled).
7. Execute the special five instruction sequence:
 - Write 55h to EECON2 in two steps (first to W, then to EECON2)
 - Write AAh to EECON2 in two steps (first to W, then to EECON2)
 - Set the WR bit
8. Enable interrupts (if using interrupts).
9. Clear the WREN bit to disable program operations.
10. At the completion of the write cycle, the WR bit is cleared and the EEIF interrupt flag bit is set. (EEIF must be cleared by firmware.) If step 1 is not implemented, then firmware should check for EEIF to be set, or WR to clear, to indicate the end of the program cycle.

EXAMPLE 4-2: EEPROM DATA WRITE

```
BSF    STATUS, RP1    ;
BSF    STATUS, RP0    ;Bank 3
BTFSF  EECON1, WR     ;Wait for
GOTO   $-1            ;write to finish
BCF    STATUS, RP0    ;Bank 2
MOVF   ADDR, W        ;Address to
MOVWF  EEADR          ;write to
MOVF   VALUE, W       ;Data to
MOVWF  EEDATA         ;write
BSF    STATUS, RP0    ;Bank 3
BCF    EECON1, EEPGD  ;Point to Data memory
BSF    EECON1, WREN   ;Enable writes
                        ;Only disable interrupts
BCF    INTCON, GIE    ;if already enabled,
                        ;otherwise discard

MOVLW  0x55           ;Write 55h to
MOVWF  EECON2         ;EECON2
MOVLW  0xAA           ;Write AAh to
MOVWF  EECON2         ;EECON2
BSF    EECON1, WR     ;Start write operation
                        ;Only enable interrupts
BSF    INTCON, GIE    ;if using interrupts,
                        ;otherwise discard
BCF    EECON1, WREN   ;Disable writes
```

4.4 Reading the FLASH Program Memory

Reading FLASH program memory is much like that of EEPROM data memory, only two NOP instructions must be inserted after the RD bit is set. These two instruction cycles that the NOP instructions execute, will be used by the microcontroller to read the data out of program memory and insert the value into the EEDATH:EEDATA registers. Data will be available following the second NOP instruction. EEDATH and EEDATA will hold their value until another read operation is initiated, or until they are written by firmware.

The steps to reading the FLASH program memory are:

1. Write the address to EEADRH:EEADR. Make sure that the address is not larger than the memory size of the PIC16F87X device.
2. Set the EEPGD bit to point to FLASH program memory.
3. Set the RD bit to start the read operation.
4. Execute two NOP instructions to allow the microcontroller to read out of program memory.
5. Read the data from the EEDATH:EEDATA registers.

EXAMPLE 4-3: FLASH PROGRAM READ

```
BSF    STATUS, RP1    ;
BCF    STATUS, RP0    ;Bank 2
MOVF   ADDR1, W       ;Write the
MOVWF  EEADR          ;address bytes
MOVF   ADDR1, W       ;for the desired
MOVWF  EEADRH         ;address to read
BSF    STATUS, RP0    ;Bank 3
BSF    EECON1, EEPGD  ;Point to Program memory
BSF    EECON1, RD     ;Start read operation
NOP    ;Required two NOPs
NOP    ;
BCF    STATUS, RP0    ;Bank 2
MOVF   EEDATA, W      ;DATA1 = EEDATA
MOVWF  DATA1         ;
MOVF   EEDATH, W      ;DATAH = EEDATH
MOVWF  DATAH         ;
```

4.5 Writing to the FLASH Program Memory

Writing to FLASH program memory is unique, in that the microcontroller does not execute instructions while programming is taking place. The oscillator continues to run and all peripherals continue to operate and queue interrupts, if enabled. Once the write operation completes (specification D133), the processor begins executing code from where it left off. The other important difference when writing to FLASH program memory, is that the WRT configuration bit, when clear, prevents any writes to program memory (see Table 4-1).

Just like EEPROM data memory, there are many steps in writing to the FLASH program memory. Both address and data values must be written to the SFRs. The EEPGD bit must be set, and the WREN bit must be set to enable writes. The WREN bit should be kept clear at all times, except when writing to the FLASH Program memory. The WR bit can only be set if the WREN bit was set in a previous operation, i.e., they both cannot be set in the same operation. The WREN bit should then be cleared by firmware after the write. Clearing the WREN bit before the write actually completes will not terminate the write in progress.

Writes to program memory must also be prefaced with a special sequence of instructions that prevent inadvertent write operations. This is a sequence of five instructions that must be executed without interruption for each byte written. These instructions must then be followed by two NOP instructions to allow the microcontroller to setup for the write operation. Once the write is complete, the execution of instructions starts with the instruction after the second NOP.

The steps to write to program memory are:

1. Write the address to EEADRH:EEADR. Make sure that the address is not larger than the memory size of the PIC16F87X device.
2. Write the 14-bit data value to be programmed in the EEDATH:EEDATA registers.
3. Set the EEPGD bit to point to FLASH program memory.
4. Set the WREN bit to enable program operations.
5. Disable interrupts (if enabled).
6. Execute the special five instruction sequence:
 - Write 55h to EECON2 in two steps (first to W, then to EECON2)
 - Write AAh to EECON2 in two steps (first to W, then to EECON2)
 - Set the WR bit
7. Execute two NOP instructions to allow the microcontroller to setup for write operation.
8. Enable interrupts (if using interrupts).
9. Clear the WREN bit to disable program operations.

At the completion of the write cycle, the WR bit is cleared and the EEIF interrupt flag bit is set. (EEIF must be cleared by firmware.) Since the microcontroller does not execute instructions during the write cycle, the firmware does not necessarily have to check either EEIF, or WR, to determine if the write had finished.

EXAMPLE 4-4: FLASH PROGRAM WRITE

```
BSF    STATUS, RP1    ;
BCF    STATUS, RP0    ;Bank 2
MOVF   ADDR_L, W      ;Write address
MOVWF  EEADR           ;of desired
MOVF   ADDR_H, W      ;program memory
MOVWF  EEADRH         ;location
MOVF   VALU_E, W      ;Write value to
MOVWF  EEDATA         ;program at
MOVF   VALU_H, W      ;desired memory
MOVWF  EEDATH         ;location
BSF    STATUS, RP0    ;Bank 3
BSF    EECON1, EEPGD  ;Point to Program memory
BSF    EECON1, WREN   ;Enable writes
                    ;Only disable interrupts
BCF    INTCON, GIE    ;if already enabled,
                    ;otherwise discard
MOVLW  0x55           ;Write 55h to
MOVWF  EECON2         ;EECON2
MOVLW  0xAA           ;Write AAh to
MOVWF  EECON2         ;EECON2
BSF    EECON1, WR      ;Start write operation
NOP                    ;Two NOPs to allow micro
NOP                    ;to setup for write
                    ;Only enable interrupts
BSF    INTCON, GIE    ;if using interrupts,
                    ;otherwise discard
BCF    EECON1, WREN   ;Disable writes
```

4.6 Write Verify

The PIC16F87X devices do not automatically verify the value written during a write operation. Depending on the application, good programming practice may dictate that the value written to memory be verified against the original value. This should be used in applications where excessive writes can stress bits near the specified endurance limits.

4.7 Protection Against Spurious Writes

There are conditions when the device may not want to write to the EEPROM data memory or FLASH program memory. To protect against these spurious write conditions, various mechanisms have been built into the PIC16F87X devices. On power-up, the WREN bit is cleared and the Power-up Timer (if enabled) prevents writes.

The write initiate sequence, and the WREN bit together, help prevent any accidental writes during brown-out, power glitches, or firmware malfunction.

4.8 Operation While Code Protected

The PIC16F87X devices have two code protect mechanisms, one bit for EEPROM data memory and two bits for FLASH program memory. Data can be read and written to the EEPROM data memory, regardless of the state of the code protection bit, CPD. When code protection is enabled and CPD cleared, external access via ICSP is disabled, regardless of the state of the program memory code protect bits. This prevents the contents of EEPROM data memory from being read out of the device.

The state of the program memory code protect bits, CP0 and CP1, do not affect the execution of instructions out of program memory. The PIC16F87X devices can always read the values in program memory, regardless of the state of the code protect bits. However, the state of the code protect bits and the WRT bit will have different effects on writing to program memory. Table 4-1 shows the effect of the code protect bits and the WRT bit on program memory.

Once code protection has been enabled for either EEPROM data memory or FLASH program memory, only a full erase of the entire device will disable code protection.

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4.9 FLASH Program Memory Write Protection

The configuration word contains a bit that write protects the FLASH program memory, called WRT. This bit can only be accessed when programming the PIC16F87X device via ICSP. Once write protection is enabled, only an erase of the entire device will disable it. When enabled, write protection prevents any writes to FLASH program memory. Write protection does not affect program memory reads.

TABLE 4-1: READ/WRITE STATE OF INTERNAL FLASH PROGRAM MEMORY

Configuration Bits			Memory Location	Internal Read	Internal Write	ICSP Read	ICSP Write
CP1	CP0	WRT					
0	0	x	All program memory	Yes	No	No	No
0	1	0	Unprotected areas	Yes	No	Yes	No
0	1	0	Protected areas	Yes	No	No	No
0	1	1	Unprotected areas	Yes	Yes	Yes	No
0	1	1	Protected areas	Yes	No	No	No
1	0	0	Unprotected areas	Yes	No	Yes	No
1	0	0	Protected areas	Yes	No	No	No
1	0	1	Unprotected areas	Yes	Yes	Yes	No
1	0	1	Protected areas	Yes	No	No	No
1	1	0	All program memory	Yes	No	Yes	Yes
1	1	1	All program memory	Yes	Yes	Yes	Yes

TABLE 4-2: REGISTERS ASSOCIATED WITH DATA EEPROM/PROGRAM FLASH

Address	Name	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Value on: POR, BOR	Value on all other RESETS
0Bh, 8Bh, 10Bh, 18Bh	INTCON	GIE	PEIE	T0IE	INTE	RBIE	T0IF	INTF	RBIF	0000 000x	0000 000u
10Dh	EEADR	EEPROM Address Register, Low Byte								xxxx xxxx	uuuu uuuu
10Fh	EEADRH	—	—	—	EEPROM Address, High Byte				xxxx xxxx	uuuu uuuu	
10Ch	EEDATA	EEPROM Data Register, Low Byte								xxxx xxxx	uuuu uuuu
10Eh	EEDATH	—	—	EEPROM Data Register, High Byte				xxxx xxxx	uuuu uuuu		
18Ch	EECON1	EEPGD	—	—	—	WRERR	WREN	WR	RD	x--- x000	x--- u000
18Dh	EECON2	EEPROM Control Register2 (not a physical register)								—	—
8Dh	PIE2	—	(1)	—	EEIE	BCLIE	—	—	CCP2IE	-r-0 0--0	-r-0 0--0
0Dh	PIR2	—	(1)	—	EEIF	BCLIF	—	—	CCP2IF	-r-0 0--0	-r-0 0--0

Legend: x = unknown, u = unchanged, r = reserved, - = unimplemented, read as '0'.

Shaded cells are not used during FLASH/EEPROM access.

Note 1: These bits are reserved; always maintain these bits clear.